

TECHNICAL DATA DATA SHEET 893, REV. A.1

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 200 Volt, 0.21 Ohm, 14A MOSFET
- Ceramic Hermetic Package
- Fast Switching
- Low R_{DS (on)}
- Electrically Equivalent to IRFY240

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_{\rm C}$ = 25°C UNLESS OTHERWISE SPECIFIED.

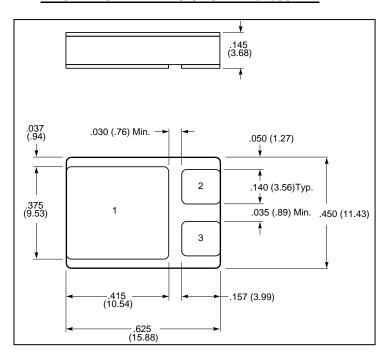
| RATING | SYMBOL | MIN. | TYP. | MAX. | UNITS |
|--|---------------------|------|------|------|-------|
| GATE TO SOURCE VOLTAGE | V_{GS} | ı | - | ±20 | Volts |
| ON-STATE DRAIN CURRENT $V_{DS} \ge 2V_{DS(on)}$, $V_{GS} = 10V$ | I _{D (on)} | - | - | 14 | Amps |
| PULSED DRAIN CURRENT @ $T_C = 25^{\circ}C$ | I _{DM} | - | - | ±56 | Amps |
| OPERATING AND STORAGE TEMPERATURE | T_{OP}/T_{STG} | -55 | - | +150 | °C |
| THERMAL RESISTANCE, JUNCTION TO CASE | $R_{\theta JC}$ | - | - | 0.72 | °C/W |
| TOTAL DEVICE DISSIPATION @ T _C = 25°C | P _D | - | - | 175 | Watts |

ELECTRICAL CHARACTERISTICS

| DRAIN TO SOURCE BREAKDOWN VOLTAGE | | BV _{DSS} | 200 | - | - | Volts |
|--|---------------------------------------|---------------------|-----|------|------|--------|
| $V_{GS} = 0V, I$ | _D = 250 μA | | | | | |
| DRAIN TO SOURCE ON-STATE VOLTAGE | | V _{DS(ON)} | - | 1.8 | 2.1 | Volts |
| | $V, I_D = 10A$ | , , | | | | |
| STATIC DRAIN TO SOURCE ON STATE RES | ISTANCE | | - | - | | |
| $V_{GS} = 10V, I_{D} = 10A$ | | $R_{DS(ON)}$ | | | 0.21 | Ω |
| $V_{GS} = 10V, I_{D} = 10A, T_{D}$ | $T_C = 125^{\circ}C$ | | | | 0.40 | |
| GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, | $I_D = 250 \mu A$ | $V_{GS(th)}$ | 2.0 | - | 4.0 | Volts |
| FORWARD TRANSCONDUCTANCE | | g _{fs} | 6.0 | - | - | S(1/Ω) |
| $V_{DS} \ge 2V_{DS(on)}$, | $I_{D} = 10A$ | | | | | ` , |
| ZERO GATE VOLTAGE DRAIN CURRENT | | | - | | | |
| $V_{DS} = 0.8xMax$. Rating, $V_{GS} = 0V$ | | I_{DSS} | | 0.1 | 0.25 | mA |
| $V_{DS} = 0.8$ xMax. Rating, $V_{GS} = 0$ V, | $\Gamma_{\rm C} = 125^{\circ}{\rm C}$ | | | 0.2 | 1.0 | |
| GATE TO SOURCE LEAKAGE FORWARD | $V_{GS} = 20V$ | I_{GSS} | - | - | 100 | nA |
| GATE TO SOURCE LEAKAGE REVERSE | $V_{GS} = -20V$ | | | | -100 | |
| TURN ON DELAY TIME V | $I_{DD} = 100 \text{V},$ | $t_{d(ON)}$ | - | 17 | - | |
| RISE TIME I _C | ₀ =14A, | t _r | | 52 | | nsec |
| TURN OFF DELAY TIME R | $L_{\rm G} = 5.0\Omega$, | $t_{d(OFF)}$ | | 36 | | |
| | $t'_{GS} = 10V$ | t _f | | 30 | | |
| DIODE FORWARD VOLTAGE $T_C = 25^{\circ}C$ | $I_{S} = 14A$ | V_{SD} | - | - | 1.5 | Volts |
| | $V_{GS} = 0V$ | | | | | |
| REVERSE RECOVERY TIME | | t _{rr} | - | | - | |
| | $I_f = I_S$, | | | 500 | | nsec |
| | 100A/μsec, | | | | | |
| | $V_{GS} = 0 V$ | C_{iss} | - | 1300 | - | |
| | $I_{DS} = 25 \text{ V}$ | C_{oss} | | 400 | | pF |
| REVERSE TRANSFER CAPACITANCE f | = 1.0MHz | C_{rss} | | 130 | | |

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MECHANICAL DIMENSIONS: in Inches / mm



SMD-1

PINOUT TABLE

| DEVICE TYPE | PIN 1 | PIN 2 | PIN 3 |
|-----------------------|-------|--------|-------|
| N CHANNEL MOSFET IN A | DRAIN | SOURCE | GATE |
| LCC-3P PACKAGE | | | |

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